

BD 233
BD 235
BD 237

**PLASTIC MEDIUM POWER
 SILICON NPN TRANSISTOR**

... designed for use in 5 to 10 Watt audio amplifiers and drivers utilizing complementary or quasi complementary circuits.

- DC Current Gain— $h_{FE} = 40$ (Min) @ $I_C = 0.15$ Adc
- BD 233, 235, 237 are complementary with BD 234, 236, 238

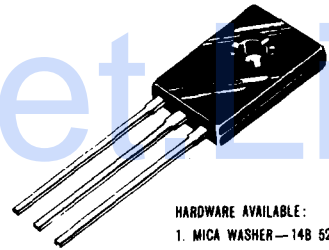
**2 AMPERE
 POWER TRANSISTOR**

NPN SILICON

**45, 60, 80 VOLTS
 25 WATTS**

MAXIMUM RATINGS

Rating	Symbol	Type	Value	Unit
Collector-Emitter Voltage	V_{CEO}	BD 233	45	Vdc
		BD 235	60	
		BD 237	80	
Collector-Base Voltage	V_{CBO}	BD 233	45	Vdc
		BD 235	60	
		BD 237	80	
Emitter-Base Voltage	V_{EBO}		5	Vdc
Collector Current	I_C		2.0	Adc
Base Current	I_B		1.0	Adc
Total Device Dissipation $T_C = 25^\circ\text{C}$	P_D		25	Watts
Operating and Storage Junction Temperature Range	T_J, T_{stg}		55 to +150	$^\circ\text{C}$



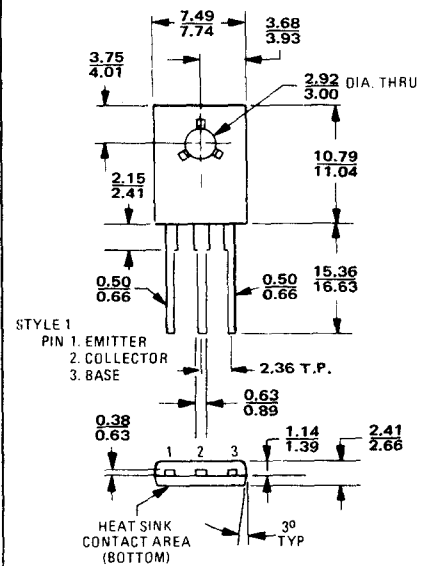
- HARDWARE AVAILABLE:**
1. MICA WASHER—148 52 600 F03
 2. LOCK WASHER—04A 52 200 F01

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θ_{JC}	50	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Type	Min	Max	Unit
Collector-Emitter Sustaining Voltage* ($I_C = 0.1$ Adc, $I_B = 0$)	V_{CEO}	BD 233	45	—	Vdc
		BD 235	60	—	
		BD 237	80	—	
Collector Cutoff Current ($V_{CB} = 45$ Vdc, $I_E = 0$) ($V_{CB} = 60$ Vdc, $I_E = 0$) ($V_{CB} = 80$ Vdc, $I_E = 0$)	I_{CBO}	BD 233	—	0.1	mA
		BD 235	—	0.1	
		BD 237	—	0.1	
Emitter Cutoff Current ($V_{BE} = 5.0$ Vdc, $I_C = 0$)	I_{EBO}		—	1.0	mA
DC current Gain ($I_C = 0.15$ A, $V_{CE} = 2$ V) ($I_C = 1$ A, $V_{CE} = 2$ V)	h_{FE1} h_{FE2}		40	—	
			25	—	
Collector-Emitter Saturation Voltage* ($I_C = 1$ Adc, $I_B = 0.1$ Adc)	$V_{CE(sat)}$		—	0.6	Vdc
Base-Emitter On Voltage* ($I_C = 1$ Adc, $V_{CE} = 2.0$ Vdc)	$V_{BE(on)}$		—	1.3	Vdc
Current-Gain-Bandwidth Product ($I_C = 250$ mA, $V_{CE} = 10$ Vdc, $f = 1.0$ MHz)	f_T		3.0	—	MHz



When mounting the device, torque not to exceed 0.07 m·kg

If lead bending is required, use suitable clamps or other supports between transistor case and point of bend.

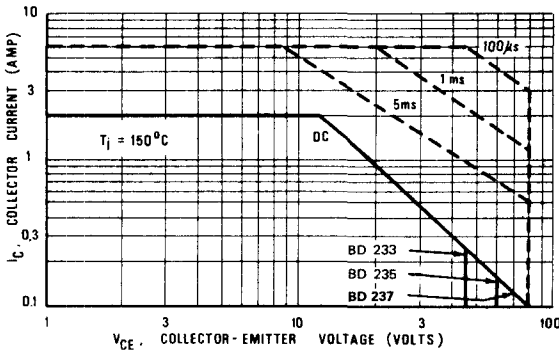
All dimensions in millimeters

CASE 77-03

* Pulse Test: Pulse Width ≤ 300 μs , Duty Cycle $\leq 2.0\%$.

BD 233
BD 235
BD 237

FIGURE 1 - ACTIVE-REGION SAFE OPERATING AREA



The Safe Operating Area Curves indicate I_C - V_{CE} limits below which the device will not enter secondary breakdown. Collector load lines for specific circuits must fall within the applicable Safe Area to avoid causing a catastrophic failure. To insure operation below the maximum T_J , power-temperature derating must be observed for both steady state and pulse power conditions.

FIGURE 2 - COLLECTOR SATURATION REGION

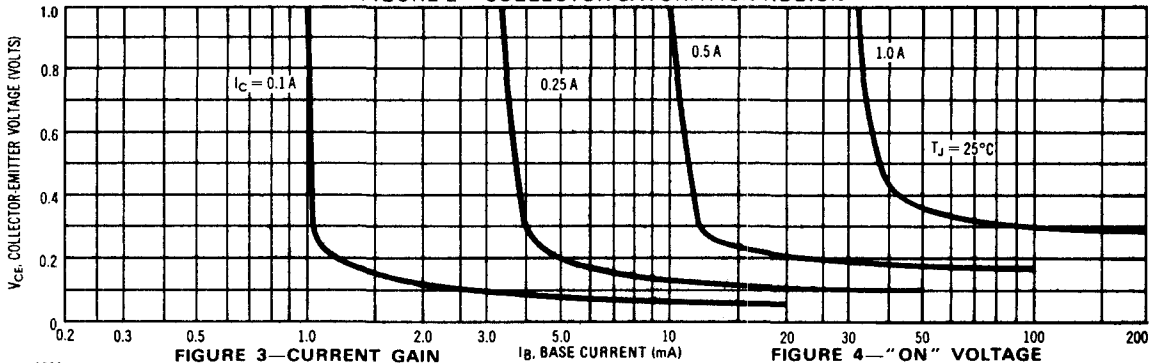


FIGURE 3 - CURRENT GAIN

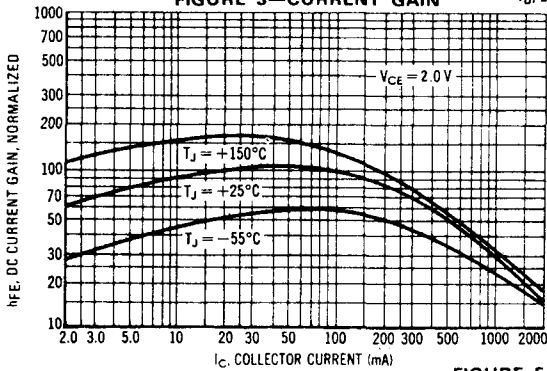


FIGURE 4 - "ON" VOLTAGE

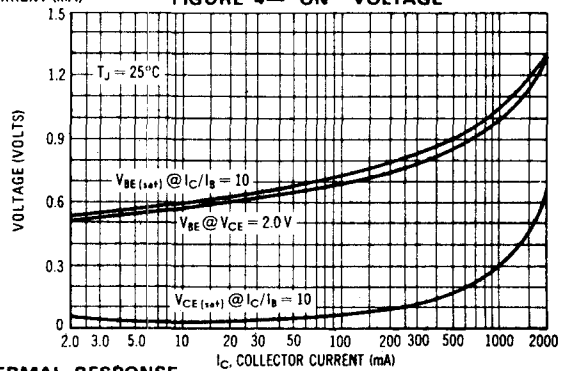


FIGURE 5 - THERMAL RESPONSE

